REMARKS

Claims 1, 5, 6, 8, 9, 13, 14, 16, 17, 21, 22 and 24-30 are pending in the above-identified application. Claims 1, 5, 6, 8, 9, 13, 14, 16, 17, 21, 22 and 24-30 were rejected. With this Amendment, claims 1, 9, 25, 26, and 30 were amended and claims 6, 8, 14, 16, 17, and 21-24 were canceled. Applicants maintain that no new matter has been added. Accordingly, claims 1, 5, 6, 8, 9, 13, 14, 16, 25-30 are at issue in the above-identified application.

Objection To Claims

Claims 6, 8 were objected to because they are duplicates of claim 5. Claims 14, 16 were objected to because they are duplicates of claim 13. Claims 22, 24 were objected to because they are duplicates of claim 21. Applicants have cancelled claims 6, 8, 14, 16, 22, and 24. Withdrawal of this rejection is respectfully requested.

Claim Rejections - 35 USC § 112

Claims 1, 5-6, 8-9, 13-14, 16-17, 21-22, 24-30 were rejected under 35 U.S.C. § 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Claim 9 was rejected under 35 U.S.C. § 112, second paragraph, as being incomplete for omitting essential structural cooperative relationships of elements, such omission amounting to a gap between the necessary structural connections. Claim 17 was rejected under 35 U.S.C. § 112, second paragraph, as being incomplete for omitting essential structural cooperative relationships of elements, such omission amounting to a gap between the necessary structural connections. Applicants have amended claims 1, 9, 25, 26, and 30 and now believe these claims meet the requirements under 35 U.S.C. § 112. Withdrawal of this rejection is respectfully requested.

Claim Rejections - 35 USC § 102

Claims 1, 5-6, 8-9, 13-14, 16-17, 21-22, 24-30 were rejected under 35 U.S.C. § 102(b) as being clearly anticipated by *Nagahama et al.* (JP 11-204, 882). Applicants respectfully traverse this rejection.

Amended claim 1 recites a semiconductor laser light admitting device comprising a stack of group III nitride semiconductor films and a current non-injection region formed on both sides of a current non-injection region, wherein said current non-injection region comprises a material expressed by a chemical formula $Al_xGa_{1-x}N$, wherein the component ratio "x" of Al is at a value in a range of $0.3 \leqq x \leqq 1.0$. *Nagahama et al.* discloses in the abstract a P-type AlGaN layer grown, and an undoped GaN layer that is also grown. A current blocking layer 14 is formed on the surface of a ridge while a P-side contact layer 13 is left below the ridge. *Nagahama et al.*, however, fails to disclose a current non-injection region comprising a material expressed by a chemical formula $Al_xGa_{1-x}N$, wherein the component ratio "x" of Al is at a value in a range of $0.3 \leqq x \leqq 1.0$, as recited in claim 1. Additionally, *Nagahama et al.* also fails to disclose that the group III nitride semiconductor films located between the active layer and the current non-injection region comprising material expressed by a chemical formula $Al_xGa_{1-x}N$ ($0.3 \leqq x \leqq 1.0$) and have a combined thickness of less than or equal to 0.2 μm but greater than zero. While *Nagahama et al.* discusses the thickness of a cladding layer and that it would be desirable to make the cladding layer 0.2 μm or less, *Nagahama et al.* fails to disclose the combined thickness of the films between the active layer and the current non-injection region. Withdrawal of this rejection is respectfully requested.

In view of the foregoing, Applicants submit that the application is in condition for allowance. Notice to that effect is requested.

Respectfully submitted,

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